



Ultraprecision Low Noise, 2.048 V/2.500 V/ 3.00 V/5.00 V XFET® Voltage References

ADR420/ADR421/ADR423/ADR425

FEATURES

Low Noise (0.1 Hz to 10 Hz)

ADR420: 1.75 μ V p-p

ADR421: 1.75 μ V p-p

ADR423: 2.0 μ V p-p

ADR425: 3.4 μ V p-p

Low Temperature Coefficient: 3 ppm/°C

Long-Term Stability: 50 ppm/1000 Hours

Load Regulation: 70 ppm/mA

Line Regulation: 35 ppm/V

Low Hysteresis: 40 ppm Typical

Wide Operating Range

ADR420: 4 V to 18 V

ADR421: 4.5 V to 18 V

ADR423: 5 V to 18 V

ADR425: 7 V to 18 V

Quiescent Current: 0.5 mA Maximum

High Output Current: 10 mA

Wide Temperature Range: -40°C to +125°C

APPLICATIONS

Precision Data Acquisition Systems

High-Resolution Converters

Battery-Powered Instrumentation

Portable Medical Instruments

Industrial Process Control Systems

Precision Instruments

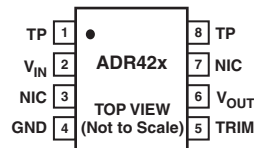
Optical Network Control Circuits

PIN CONFIGURATION

Surface-Mount Packages

8-Lead SOIC

8-Lead Mini_SOIC



NIC = NO INTERNAL CONNECTION
TP = TEST PIN (DO NOT CONNECT)

GENERAL DESCRIPTION

The ADR42x series are ultraprecision second-generation XFET voltage references featuring low noise, high accuracy, and excellent long-term stability in a SOIC and Mini_SOIC footprints. Patented temperature drift curvature correction technique and XFET (eXtra implanted junction FET) technology minimize nonlinearity of the voltage change with temperature. The XFET architecture offers superior accuracy and thermal hysteresis to the bandgap references. It also operates at lower power and lower supply headroom than the Buried Zener references.

The superb noise, stable, and accurate characteristics of ADR42x make them ideal for precision conversion applications such as optical network and medical equipment. The ADR42x trim terminal can also be used to adjust the output voltage over a $\pm 0.5\%$ range without compromising any other performance. The ADR42x series voltage references offer two electrical grades and are specified over the extended industrial temperature range of -40°C to +125°C. Devices are available in 8-lead SOIC-8 or 30% smaller 8-lead Mini_SOIC-8 packages.

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Table I. ADR42x Products

ADR420 Products	Output Voltage V_O	Initial Accuracy mV	Initial Accuracy %	Tempco ppm/°C
ADR420	2.048	1, 3	0.05, 0.15	3, 10
ADR421	2.50	1, 3	0.04, 0.12	3, 10
ADR423	3.00	1.5, 4	0.04, 0.12	3, 10
ADR425	5.00	2, 6	0.04, 0.12	3, 10

ADR42x—SPECIFICATIONS

ADR420 ELECTRICAL SPECIFICATIONS (@ $V_{IN} = 5.0\text{ V}$ to 15.0 V , $T_A = 25^\circ\text{C}$, unless otherwise noted.)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output Voltage	V_O		2.045	2.048	2.051	V
Initial Accuracy	V_{OERR}		-3		+3	mV
			-0.15		+0.15	%
Output Voltage	V_O		2.047	2.048	2.049	V
Initial Accuracy	V_{OERR}		-1		+1	mV
			-0.05		+0.05	%
Temperature Coefficient	TCV_O	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		2	10	ppm/ $^\circ\text{C}$
				1	3	ppm/ $^\circ\text{C}$
Supply Voltage Headroom	$V_{IN} - V_O$		2			V
Line Regulation	$\Delta V_O / \Delta V_{IN}$	$V_{IN} = 5\text{ V to }18\text{ V}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$		10	35	ppm/V
Load Regulation	$\Delta V_O / \Delta I_{LOAD}$	$I_{LOAD} = 0\text{ mA to }10\text{ mA}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$			70	ppm/mA
Quiescent Current	I_{IN}	No Load $-40^\circ\text{C} < T_A < +125^\circ\text{C}$		390	500	μA
					600	μA
Voltage Noise	e_N p-p	0.1 Hz to 10 Hz		1.75		$\mu\text{V p-p}$
Voltage Noise Density	e_N	1 kHz		60		nV/ $\sqrt{\text{Hz}}$
Turn-On Settling Time	t_R			10		μs
Long-Term Stability	ΔV_O	1,000 Hours		50		ppm
Output Voltage Hysteresis	V_{O_HYS}			40		ppm
Ripple Rejection Ratio	RRR	$f_{IN} = 10\text{ kHz}$		75		dB
Short Circuit to GND	I_{SC}			27		mA

Specifications subject to change without notice.

ADR421 ELECTRICAL SPECIFICATIONS (@ $V_{IN} = 5.0\text{ V}$ to 15.0 V , $T_A = 25^\circ\text{C}$, unless otherwise noted.)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output Voltage	V_O		2.497	2.500	2.503	V
Initial Accuracy	V_{OERR}		-3		+3	mV
			-0.12		+0.12	%
Output Voltage	V_O		2.499	2.500	2.501	V
Initial Accuracy	V_{OERR}		-1		+1	mV
			-0.04		+0.04	%
Temperature Coefficient	TCV_O	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		2	10	ppm/ $^\circ\text{C}$
				1	3	ppm/ $^\circ\text{C}$
Supply Voltage Headroom	$V_{IN} - V_O$		2			V
Line Regulation	$\Delta V_O / \Delta V_{IN}$	$V_{IN} = 5\text{ V to }18\text{ V}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$		10	35	ppm/V
Load Regulation	$\Delta V_O / \Delta I_{LOAD}$	$I_{LOAD} = 0\text{ mA to }10\text{ mA}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$			70	ppm/mA
Quiescent Current	I_{IN}	No Load $-40^\circ\text{C} < T_A < +125^\circ\text{C}$		390	500	μA
					600	μA
Voltage Noise	e_N p-p	0.1 Hz to 10 Hz		1.75		$\mu\text{V p-p}$
Voltage Noise Density	e_N	1 kHz		80		nV/ $\sqrt{\text{Hz}}$
Turn-On Settling Time	t_R			10		μs
Long-Term Stability	ΔV_O	1,000 Hours		50		ppm
Output Voltage Hysteresis	V_{O_HYS}			40		ppm
Ripple Rejection Ratio	RRR	$f_{IN} = 10\text{ kHz}$		75		dB
Short Circuit to GND	I_{SC}			27		mA

Specifications subject to change without notice.

ADR423 ELECTRICAL SPECIFICATIONS (@ $V_{IN} = 5.0\text{ V}$ to 15.0 V , $T_A = 25^\circ\text{C}$, unless otherwise noted.)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output Voltage	V_O		2.996	3.000	3.004	V
Initial Accuracy	V_{OERR}		-4		+4	mV
			-0.13		+0.13	%
Output Voltage	V_O		2.9985	3.000	3.0015	V
Initial Accuracy	V_{OERR}		-1.5		+1.5	mV
			-0.04		+0.04	%
Temperature Coefficient	TCV_O	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		2	10	ppm/ $^\circ\text{C}$
				1	3	ppm/ $^\circ\text{C}$
Supply Voltage Headroom	$V_{IN} - V_O$		2			V
Line Regulation	$\Delta V_O / \Delta V_{IN}$	$V_{IN} = 5\text{ V to } 18\text{ V}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$		10	35	ppm/V
Load Regulation	$\Delta V_O / \Delta I_{LOAD}$	$I_{LOAD} = 0\text{ mA to } 10\text{ mA}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$			70	ppm/mA
Quiescent Current	I_{IN}	No Load $-40^\circ\text{C} < T_A < +125^\circ\text{C}$		390	500	μA
					600	μA
Voltage Noise	e_N p-p	0.1 Hz to 10 Hz		2		$\mu\text{V p-p}$
Voltage Noise Density	e_N	1 kHz		90		nV/ $\sqrt{\text{Hz}}$
Turn-On Settling Time	t_R			10		μs
Long-Term Stability	ΔV_O	1,000 Hours		50		ppm
Output Voltage Hysteresis	V_{O_HYS}			40		ppm
Ripple Rejection Ratio	RRR	$f_{IN} = 10\text{ kHz}$		75		dB
Short Circuit to GND	I_{SC}			27		mA

Specifications subject to change without notice.

ADR425 ELECTRICAL SPECIFICATIONS (@ $V_{IN} = 7.0\text{ V}$ to 15.0 V , $T_A = 25^\circ\text{C}$, unless otherwise noted.)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output Voltage	V_O		4.994	5.000	5.006	V
Initial Accuracy	V_{OERR}		-6		+6	mV
			-0.12		+0.12	%
Output Voltage	V_O		4.998	5.000	5.002	V
Initial Accuracy	V_{OERR}		-2		+2	mV
			-0.04		+0.04	%
Temperature Coefficient	TCV_O	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		2	10	ppm/ $^\circ\text{C}$
				1	3	ppm/ $^\circ\text{C}$
Supply Voltage Headroom	$V_{IN} - V_O$		2			V
Line Regulation	$\Delta V_O / \Delta V_{IN}$	$V_{IN} = 7\text{ V to } 18\text{ V}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$		10	35	ppm/V
Load Regulation	$\Delta V_O / \Delta I_{LOAD}$	$I_{LOAD} = 0\text{ mA to } 10\text{ mA}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$			70	ppm/mA
Quiescent Current	I_{IN}	No Load $-40^\circ\text{C} < T_A < +125^\circ\text{C}$		390	500	μA
					600	μA
Voltage Noise	e_N p-p	0.1 Hz to 10 Hz		3.4		$\mu\text{V p-p}$
Voltage Noise Density	e_N	1 kHz		110		nV/ $\sqrt{\text{Hz}}$
Turn-On Settling Time	t_R			10		μs
Long-Term Stability	ΔV_O	1,000 Hours		50		ppm
Output Voltage Hysteresis	V_{O_HYS}			40		ppm
Ripple Rejection Ratio	RRR	$f_{IN} = 10\text{ kHz}$		75		dB
Short Circuit to GND	I_{SC}			27		mA

Specifications subject to change without notice.

ADR420/ADR421/ADR423/ADR425

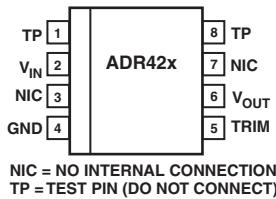
ABSOLUTE MAXIMUM RATINGS*

Supply Voltage 18 V
 Output Short-Circuit Duration to GND Indefinite
 Storage Temperature Range
 R, RM Packages -65°C to +150°C
 Operating Temperature Range
 ADR42x -40°C to +125°C
 Junction Temperature Range
 R, RM Packages -65°C to +150°C
 Lead Temperature Range (Soldering, 60 sec) 300°C

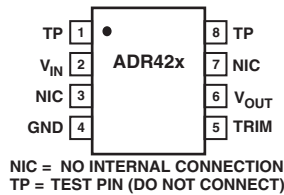
*Absolute maximum ratings apply at 25°C, unless otherwise noted.

PIN CONFIGURATIONS

SOIC-8



Mini_SOIC-8



PIN FUNCTION DESCRIPTIONS

Pin	Mnemonic	Description
1, 8	TP	Test Pin. There are actual connections in TP pins but they are reserved for factory testing purposes. Users should not connect anything to TP pins, otherwise the device may not function properly.
2	V _{IN}	Input Voltage
3, 7	NIC	No Internal Connect. NICs have no internal connections.
4	GND	Ground Pin = 0 V
5	TRIM	Trim Terminal. It can be used to adjust the output voltage over a ±0.5% range without affecting the temperature coefficient.
6	V _{OUT}	Output Voltage

Package Type	θ _{JA} *	Unit
8-Lead Mini_SOIC (RM)	190	°C/W
8-Lead SOIC (R)	130	°C/W

*θ_{JA} is specified for the worst-case conditions, i.e., θ_{JA} is specified for device soldered in circuit board for surface-mount packages.

ORDERING GUIDE

Model	Output Voltage V _O	Initial Accuracy		Temperature Coefficient ppm/°C	Package Description	Package Option	Top Mark	Number of Parts per Reel	Temperature Range °C
		mV	%						
ADR420AR	2.048	3	0.15	10	SOIC	SO-8	ADR420	98	-40 to +125
ADR420AR-Reel7	2.048	3	0.15	10	SOIC	SO-8	ADR420	3,000	-40 to +125
ADR420BR	2.048	1	0.05	3	SOIC	SO-8	ADR420	98	-40 to +125
ADR420BR-Reel7	2.048	1	0.05	3	SOIC	SO-8	ADR420	3,000	-40 to +125
ADR420ARM-Reel7	2.048	3	0.15	10	Mini_SOIC	RM-8	R4A	1,000	-40 to +125
ADR421AR	2.50	3	0.12	10	SOIC	SO-8	ADR421	98	-40 to +125
ADR421AR-Reel7	2.50	3	0.12	10	SOIC	SO-8	ADR421	3,000	-40 to +125
ADR421BR	2.50	1	0.04	3	SOIC	SO-8	ADR421	98	-40 to +125
ADR421BR-Reel7	2.50	1	0.04	3	SOIC	SO-8	ADR421	3,000	-40 to +125
ADR421ARM-Reel7	2.50	3	0.12	10	Mini_SOIC	RM-8	R5A	1,000	-40 to +125
ADR423AR	3.00	4	0.13	10	SOIC	SO-8	ADR423	98	-40 to +125
ADR423AR-Reel7	3.00	4	0.13	10	SOIC	SO-8	ADR423	3,000	-40 to +125
ADR423BR	3.00	1.5	0.04	3	SOIC	SO-8	ADR423	98	-40 to +125
ADR423BR-Reel7	3.00	1.5	0.04	3	SOIC	SO-8	ADR423	3,000	-40 to +125
ADR423ARM-Reel7	3.00	4	0.13	10	Mini_SOIC	RM-8		1,000	-40 to +125
ADR425AR	5.00	6	0.12	10	SOIC	SO-8	ADR425	98	-40 to +125
ADR425AR-Reel7	5.00	6	0.12	10	SOIC	SO-8	ADR425	3,000	-40 to +125
ADR425BR	5.00	2	0.04	3	SOIC	SO-8	ADR425	98	-40 to +125
ADR425BR-Reel7	5.00	2	0.04	3	SOIC	SO-8	ADR425	3,000	-40 to +125
ADR425ARM-Reel7	5.00	6	0.12	10	Mini_SOIC	RM-8	R7A	1,000	-40 to +125

CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADR42x features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high-energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



PARAMETER DEFINITIONS

Temperature Coefficient

The change of output voltage over the operating temperature range and normalized by the output voltage at 25°C, expressed in ppm/°C. The equation follows:

$$TCV_o \text{ (ppm/°C)} = \frac{V_o(T_2) - V_o(T_1)}{V_o(25^\circ\text{C}) \times (T_2 - T_1)} \times 10^6$$

where

$V_o(25^\circ\text{C}) = V_o$ at 25°C

$V_o(T_1) = V_o$ at Temperature 1

$V_o(T_2) = V_o$ at Temperature 2.

Line Regulation

The change in output voltage due to a specified change in input voltage. It includes the effects of self-heating. Line regulation is expressed in either percent per volt, parts-per-million per volt, or microvolts per volt change in input voltage

Load Regulation

The change in output voltage due to a specified change in load current. It includes the effects of self-heating. Load regulation is expressed in either microvolts per milliampere, parts-per-million per milliampere, or ohms of dc output resistance.

Long-Term Stability

Typical shift of output voltage at 25°C on a sample of parts subjected to operation life test of 1000 hours at 125°C:

$$\Delta V_o = V_o(t_0) - V_o(t_1)$$

$$\Delta V_o \text{ (ppm)} = \frac{V_o(t_0) - V_o(t_1)}{V_o(t_0)} \times 10^6$$

where

$V_o(t_0) = V_o$ at 25°C at Time 0

$V_o(t_1) = V_o$ at 25°C after 1,000 hours operation at 125°C.

Thermal Hysteresis

Thermal hysteresis is defined as the change of output voltage after the device is cycled through temperature from +25°C to -40°C to +125°C and back to +25°C. This is a typical value from a sample of parts put through such a cycle.

$$V_{O_HYS} = V_o(25^\circ\text{C}) - V_{O_TC}$$

$$V_{O_HYS} \text{ (ppm)} = \frac{V_o(25^\circ\text{C}) - V_{O_TC}}{V_o(25^\circ\text{C})} \times 10^6$$

where

$V_o(25^\circ\text{C}) = V_o$ at 25°C

$V_{O_TC} = V_o$ at 25°C after temperature cycle at +25°C to -40°C to +125°C and back to +25°C.

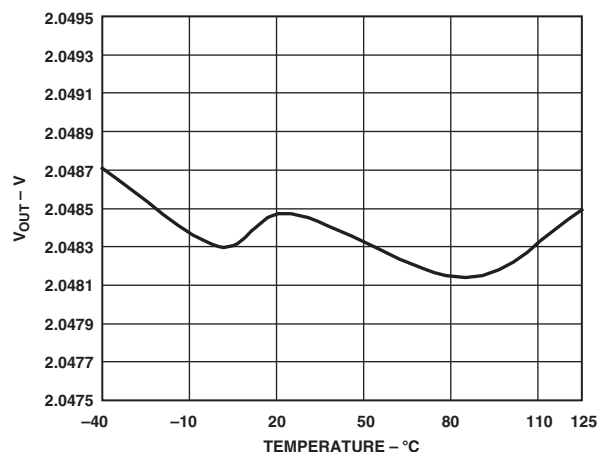
Input Capacitor

Input capacitors are not required on the ADR42x. There is no limit for the value of the capacitor used on the input, but a 1 µF to 10 µF capacitor on the input will improve transient response in applications where the supply suddenly changes. An additional 0.1 µF in parallel will also help to reduce noise from the supply.

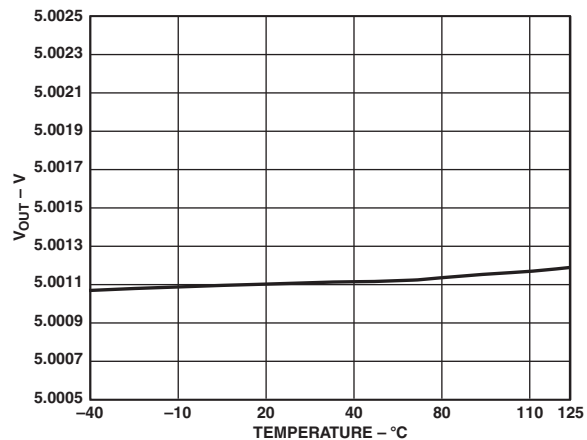
Output Capacitor

The ADR42x does not need output capacitors for stability under any load condition. An output capacitor, typically 0.1 µF, will filter out any low-level noise voltage and will not affect the operation of the part. On the other hand, the load transient response can be improved with an additional 1 µF to 10 µF output capacitor in parallel. A capacitor here will act as a source of stored energy for sudden increase in load current. The only parameter that will degrade, by adding an output capacitor, is turn-on time and it depends on the size of the capacitor chosen.

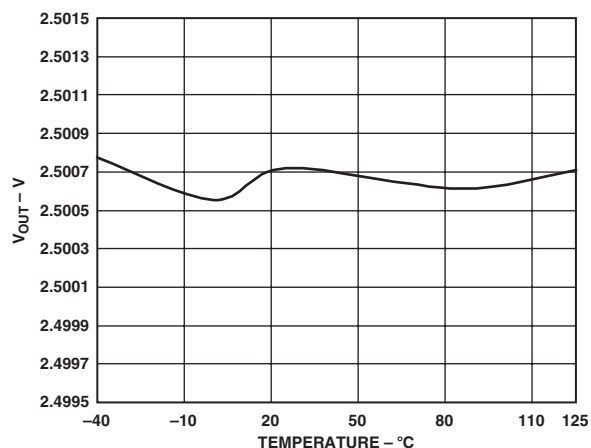
ADR42x Series—Typical Performance Characteristics



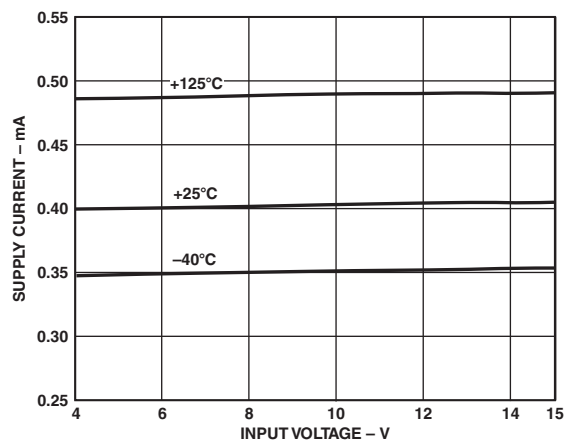
TPC 1. ADR420 Typical Output Voltage vs. Temperature



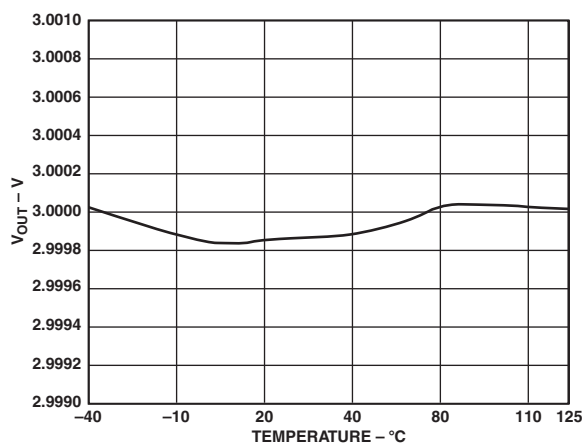
TPC 4. ADR425 Typical Output Voltage vs. Temperature



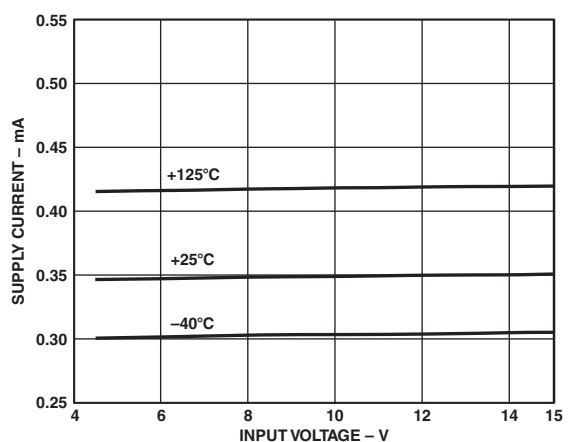
TPC 2. ADR421 Typical Output Voltage vs. Temperature



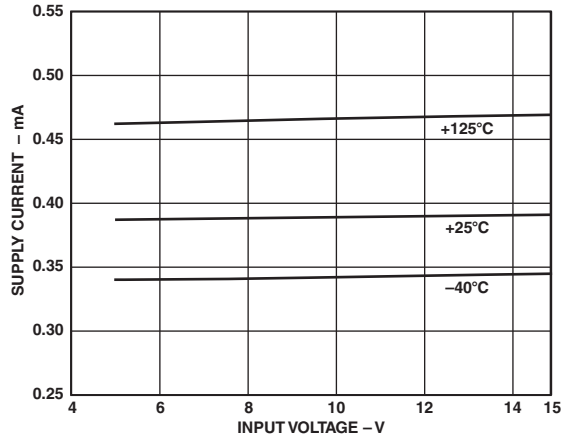
TPC 5. ADR420 Supply Current vs. Input Voltage



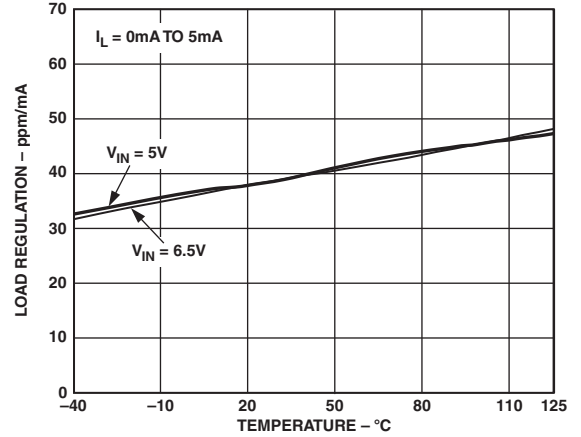
TPC 3. ADR423 Typical Output Voltage vs. Temperature



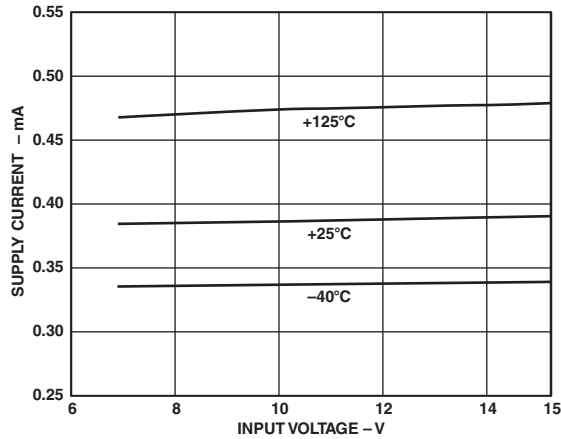
TPC 6. ADR421 Supply Current vs. Input Voltage



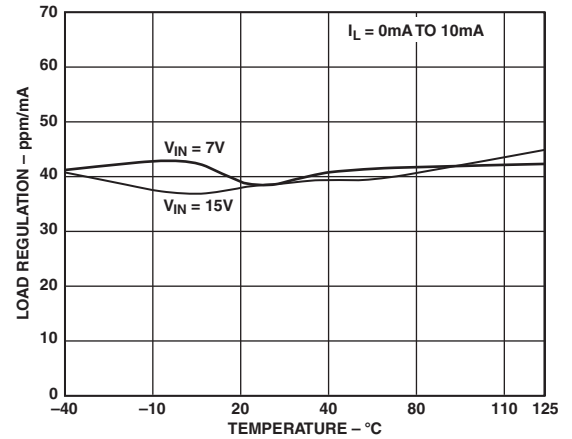
TPC 7. ADR423 Supply Current vs. Input Voltage



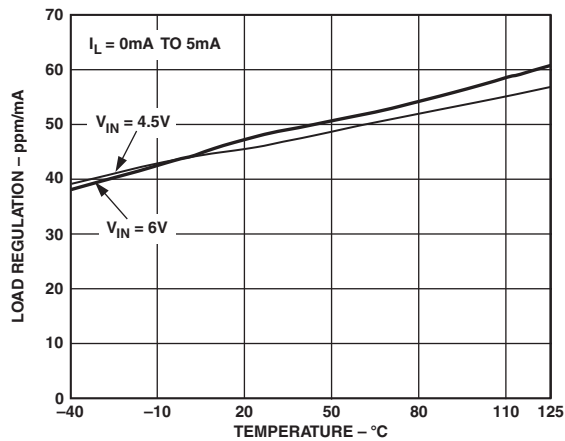
TPC 10. ADR421 Load Regulation vs. Temperature



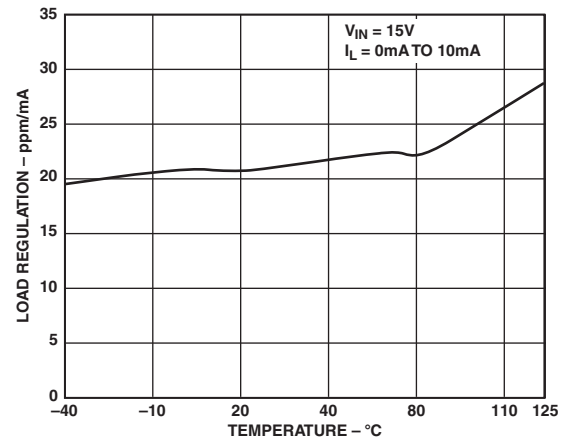
TPC 8. ADR425 Supply Current vs. Input Voltage



TPC 11. ADR423 Load Regulation vs. Temperature

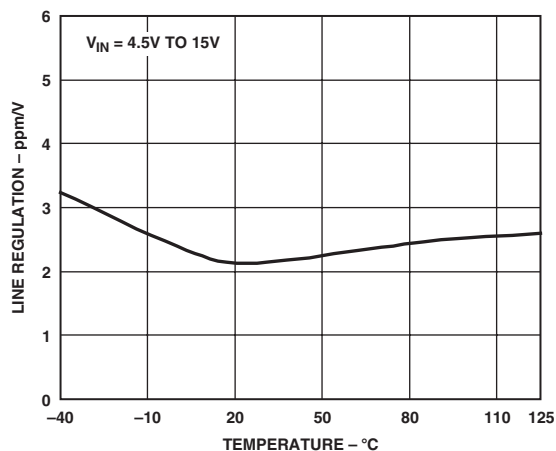


TPC 9. ADR420 Load Regulation vs. Temperature

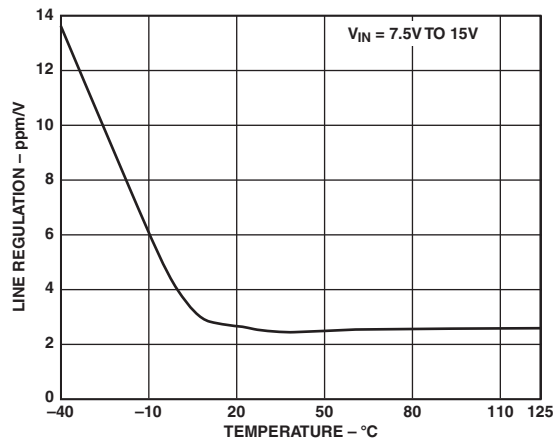


TPC 12. ADR425 Load Regulation vs. Temperature

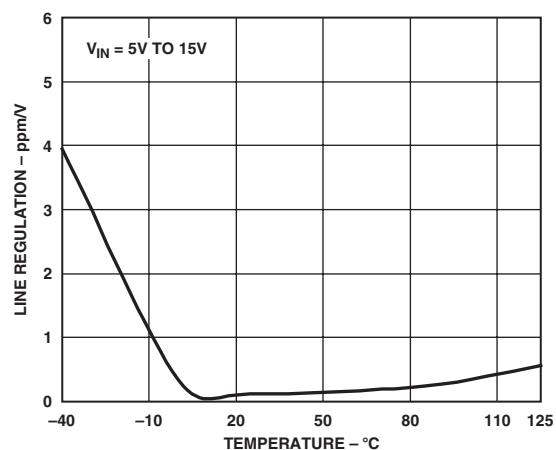
ADR420/ADR421/ADR423/ADR425



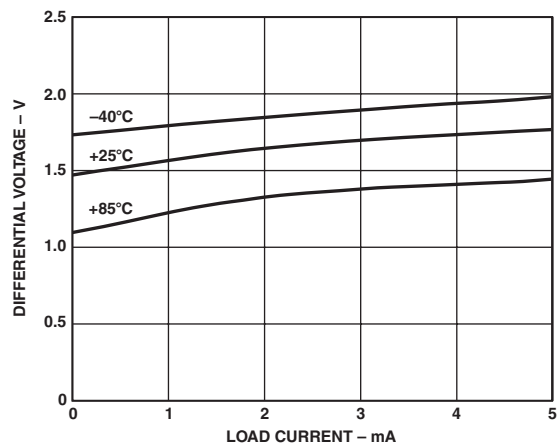
TPC 13. ADR420 Line Regulation vs. Temperature



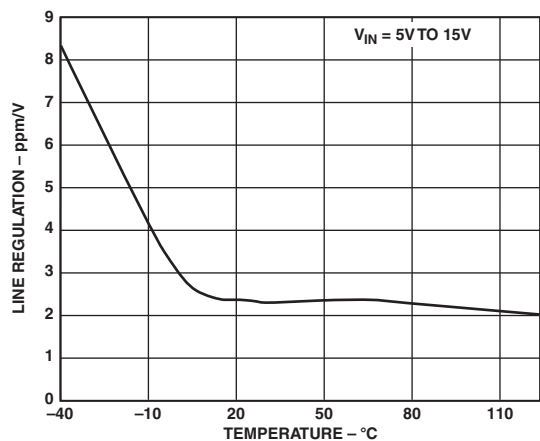
TPC 16. ADR425 Line Regulation vs. Temperature



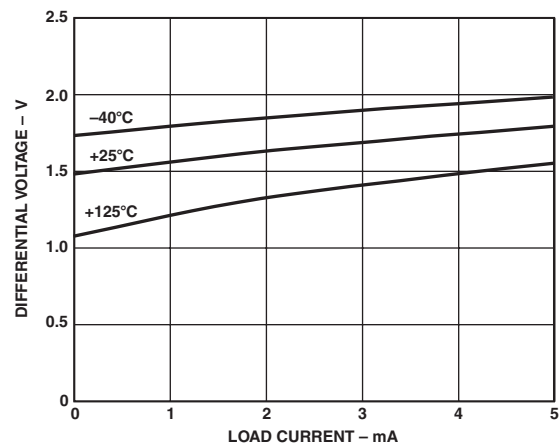
TPC 14. ADR421 Line Regulation vs. Temperature



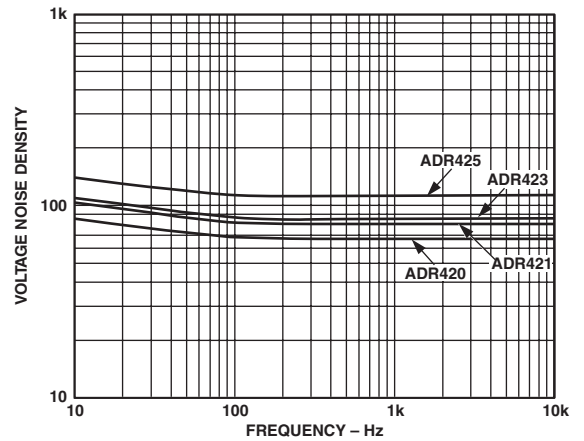
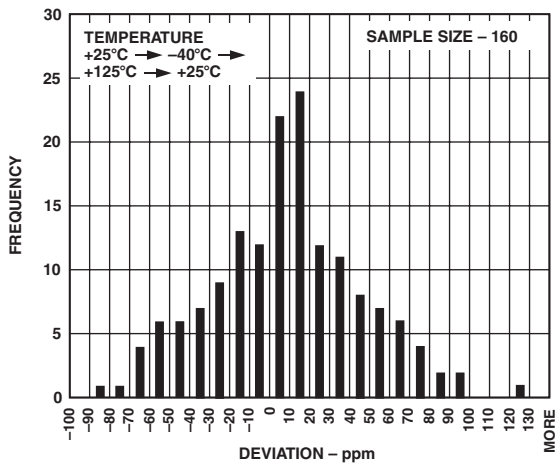
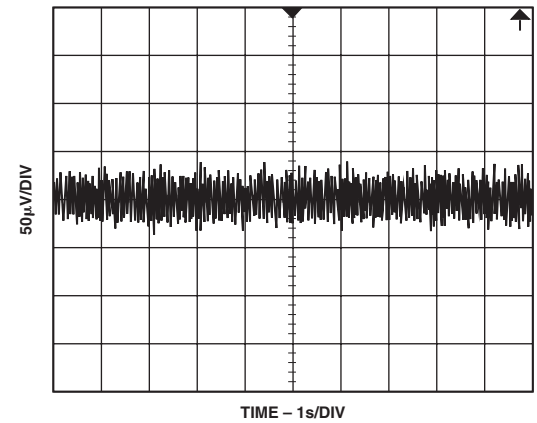
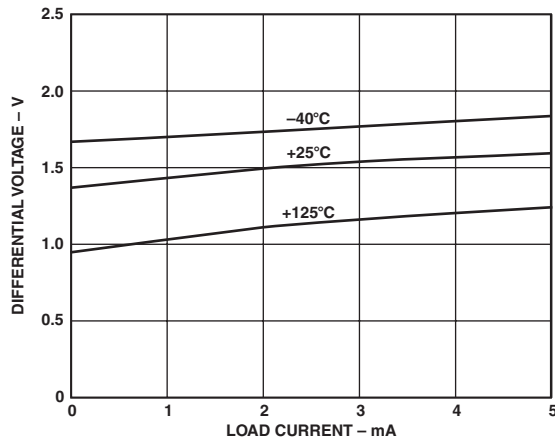
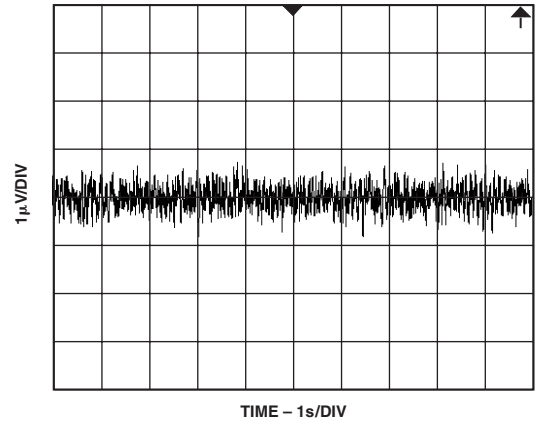
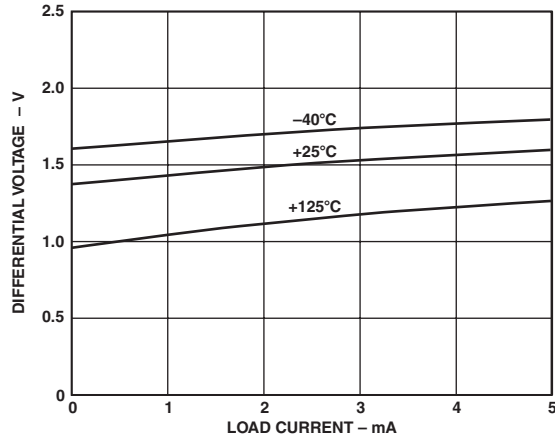
TPC 17. ADR420 Minimum Input-Output Voltage Differential vs. Load Current



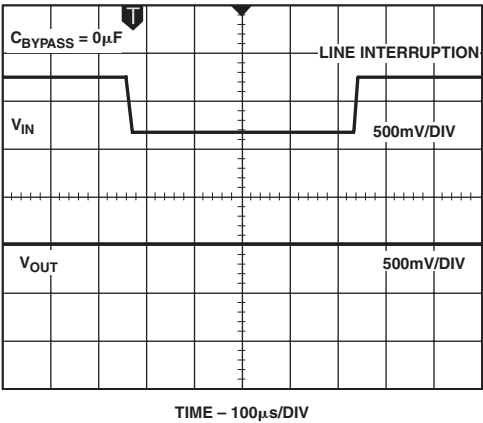
TPC 15. ADR423 Line Regulation vs. Temperature



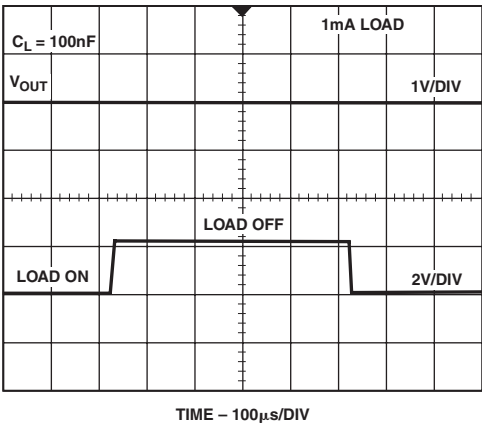
TPC 18. ADR421 Minimum Input-Output Voltage Differential vs. Load Current



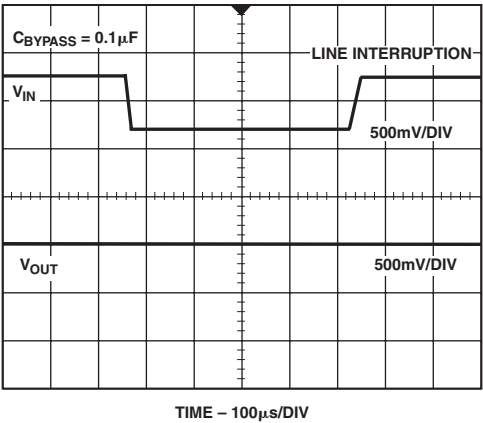
ADR420/ADR421/ADR423/ADR425



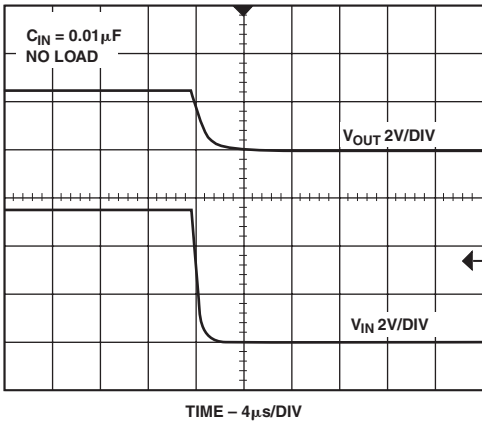
TPC 25. ADR421 Line Transient Response



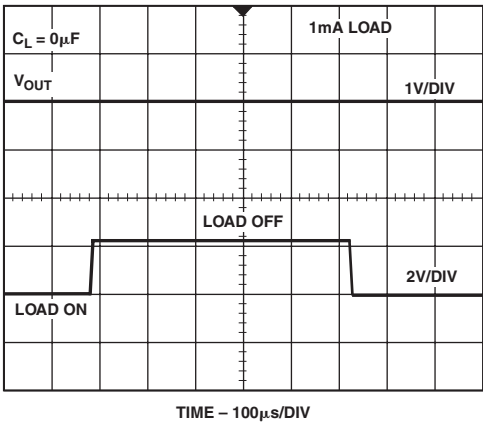
TPC 28. ADR421 Load Transient Response



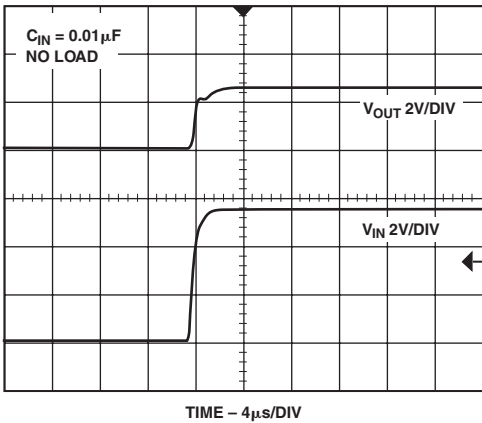
TPC 26. ADR421 Line Transient Response



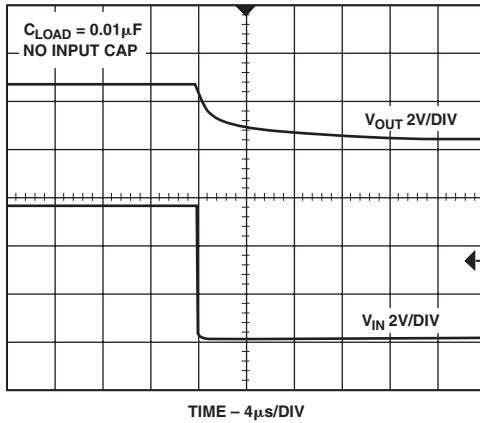
TPC 29. ADR421 Turn-Off Response



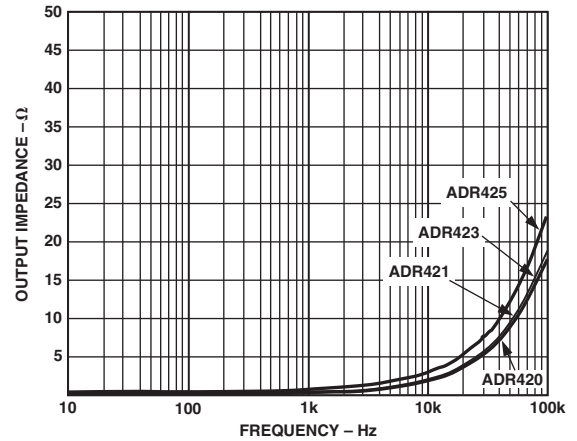
TPC 27. ADR421 Load Transient Response



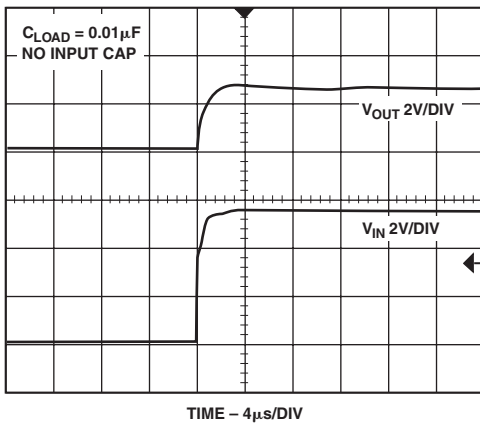
TPC 30. ADR421 Turn-On Response



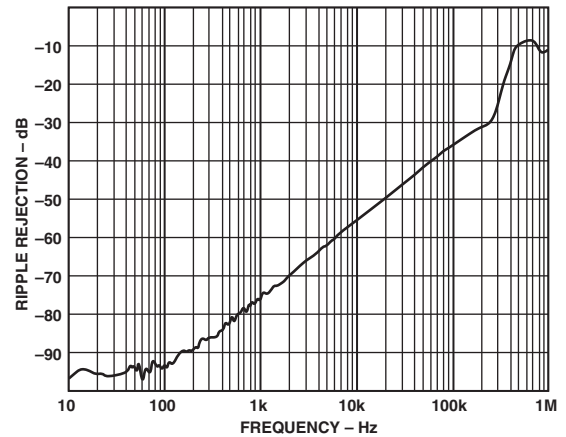
TPC 31. ADR421 Turn-Off Response



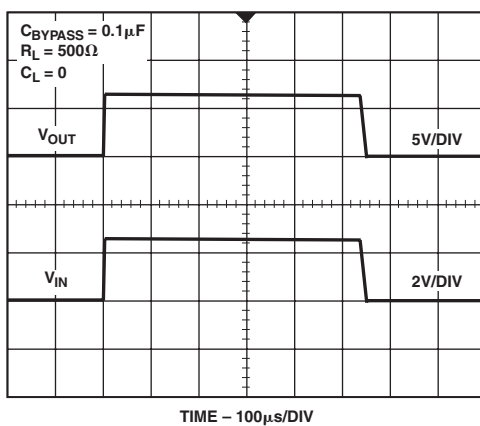
TPC 34. Output Impedance vs. Frequency



TPC 32. ADR421 Turn-On Response



TPC 35. Ripple Rejection vs. Frequency



TPC 33. ADR421 Turn-On/Turn-Off Response

ADR420/ADR421/ADR423/ADR425

THEORY OF OPERATION

The ADR42x series of references uses a new reference generation technique known as XFET (eXtra implanted junction FET). This technique yields a reference with low supply current, good thermal hysteresis, and exceptionally low noise. The core of the XFET reference consists of two junction field-effect transistors (JFET), one of which has an extra channel implant to raise its pinch-off voltage. By running the two JFETs at the same drain current, the difference in pinch-off voltage can be amplified and used to form a highly stable voltage reference.

The intrinsic reference voltage is around 0.5 V with a negative temperature coefficient of about $-120 \text{ ppm}/^\circ\text{C}$. This slope is essentially constant to the dielectric constant of silicon and can be closely compensated by adding a correction term generated in the same fashion as the proportional-to-temperature (PTAT) term used to compensate bandgap references. The big advantage over a bandgap reference is that the intrinsic temperature coefficient is some thirty times lower (therefore requiring less correction), resulting in much lower noise since most of the noise of a bandgap reference comes from the temperature compensation circuitry.

Figure 1 shows the basic topology of the ADR42x series. The temperature correction term is provided by a current source with a value designed to be proportional to absolute temperature. The general equation is:

$$V_{OUT} = G \times (\Delta V_P - R1 \times I_{PTAT}) \quad (1)$$

where G is the gain of the reciprocal of the divider ratio, ΔV_P is the difference in pinch-off voltage between the two JFETs, and I_{PTAT} is the positive temperature coefficient correction current. ADR42x are created by on-chip adjustment of $R2$ and $R3$ to achieve 2.048 V or 2.500 V at the reference output respectively.

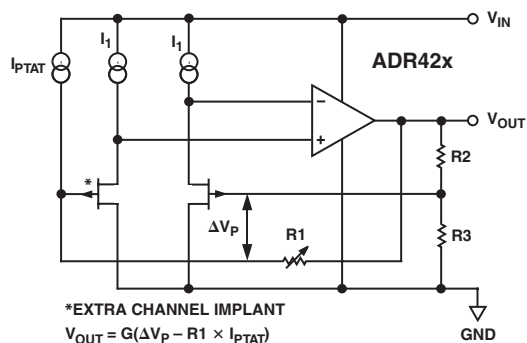


Figure 1. Simplified Schematic

Device Power Dissipation Considerations

The ADR42x family of references is guaranteed to deliver load currents to 10 mA with an input voltage that ranges from 4.5 V to 18 V. When these devices are used in applications at higher current, users should account for the temperature effects due to the power dissipation increases with the following equation:

$$T_J = P_D \times \theta_{JA} + T_A \quad (2)$$

where T_J and T_A are the junction and ambient temperatures, respectively, P_D is the device power dissipation, and θ_{JA} is the device package thermal resistance.

Basic Voltage Reference Connections

Voltage references, in general, require a bypass capacitor connected from V_{OUT} to GND. The circuit in Figure 2 illustrates the basic configuration for the ADR42x family of references. Other than a $0.1 \mu\text{F}$ capacitor at the output to help improve noise suppression, a large output capacitor at the output is not required for circuit stability.

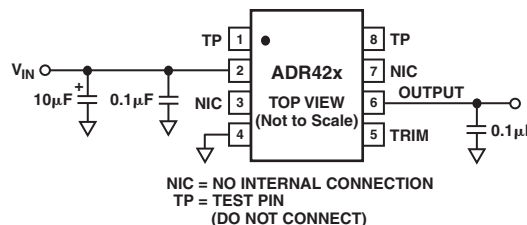


Figure 2. Basic Voltage Reference Configuration

Noise Performance

The noise generated by the ADR42x family of references is typically less than $2 \mu\text{V p-p}$ over the 0.1 Hz to 10 Hz band for ADR420, ADR421, and ADR423. TPC 22 shows the 0.1 Hz to 10 Hz noise of the ADR421, which is only $1.75 \mu\text{V p-p}$. The noise measurement is made with a bandpass filter made of a 2-pole high-pass filter with a corner frequency at 0.1 Hz and a 2-pole low-pass filter with a corner frequency at 10 Hz.

Turn-On Time

Upon application of power (cold start), the time required for the output voltage to reach its final value within a specified error band is defined as the turn-on settling time. Two components normally associated with this are the time for the active circuits to settle, and the time for the thermal gradients on the chip to stabilize. TPC 29 through TPC 33, inclusive, show the turn-on settling time for the ADR421.

APPLICATIONS SECTION

OUTPUT ADJUSTMENT

The ADR42x trim terminal can be used to adjust the output voltage over a $\pm 0.5\%$ range. This feature allows the system designer to trim system errors out by setting the reference to a voltage other than the nominal. This is also helpful if the part is used in a system at temperature to trim out any error. Adjustment of the output has negligible effect on the temperature performance of the device. To avoid degrading temperature coefficient, both the trimming potentiometer and the two resistors need to be low temperature coefficient types, preferably $<100 \text{ ppm}/^\circ\text{C}$.

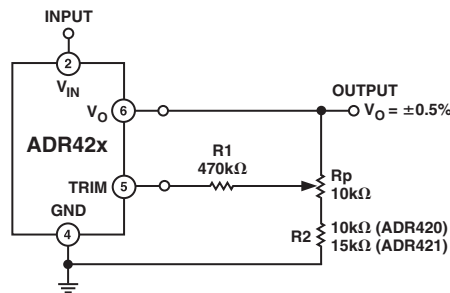


Figure 3. Output Trim Adjustment

Reference for Converters in Optical Network Control Circuits

In the upcoming high-capacity, all-optical router network, Figure 4 employs arrays of micromirrors to direct and route optical signals from fiber to fiber, without first converting them to electrical form, which reduces the communication speed. The tiny micromechanical mirrors are positioned so that each is illuminated by a single wavelength that carries unique information and can be passed to any desired input and output fiber. The mirrors are tilted by the dual-axis actuators controlled by precision ADCs and DACs within the system. Due to the microscopic movement of the mirrors, not only is the precision of the converters important, but the noise associated with these controlling converters is also extremely critical, because total noise within the system can be multiplied by the numbers of converters employed. As a result, the ADR42x is necessary for this application for its exceptional low noise to maintain the stability of the control loop.

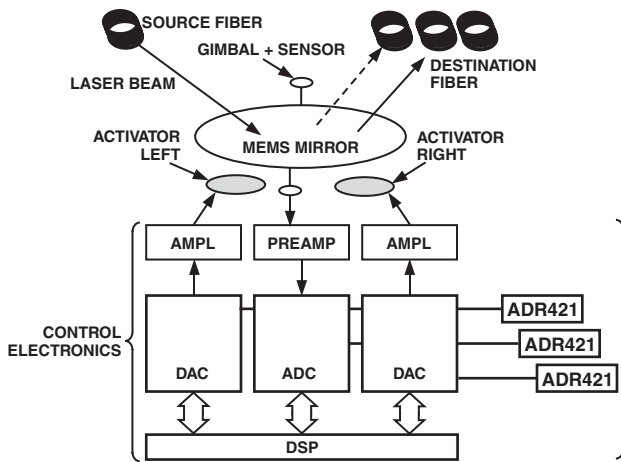


Figure 4. All-Optical Router Network

A Negative Precision Reference without Precision Resistors

In many current-output CMOS DAC applications, where the output signal voltage must be of the same polarity as the reference voltage, it is often required to reconfigure a current-switching DAC into a voltage-switching DAC through the use of a 1.25 V reference, an op amp, and a pair of resistors. Using a current-switching DAC directly requires the need for an additional operational amplifier at the output to reinvert the signal. A negative voltage reference is then desirable from the point that an additional operational amplifier is not required for either reinversion (current-switching mode) or amplification (voltage-switching mode) of the DAC output voltage. In general, any positive voltage reference can be converted into a negative voltage reference through the use of an operational amplifier and a pair of matched resistors in an inverting configuration. The disadvantage to that approach is that the largest single source of error in the circuit is the relative matching of the resistors used.

A negative reference can easily be generated by adding a precision op amp and configuring as in Figure 5. V_{OUT} is at virtual ground and, therefore, the negative reference can be taken directly from the output of the op amp. The op amp must be dual supply, low offset, and have rail-to-rail capability if negative supply voltage is close to the reference output.

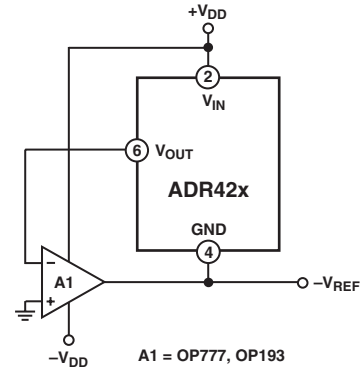


Figure 5. Negative Reference

High-Voltage Floating Current Source

The circuit of Figure 6 can be used to generate a floating current source with minimal self-heating. This particular configuration can operate on high supply voltages determined by the breakdown voltage of the N-channel JFET.

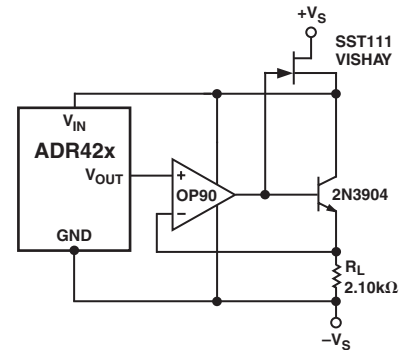


Figure 6. High-Voltage Floating Current Source

Kelvin Connections

In many portable instrumentation applications, where PC board cost and area go hand-in-hand, circuit interconnects are very often of dimensionally minimum width. These narrow lines can cause large voltage drops if the voltage reference is required to provide load currents to various functions. In fact, a circuit's interconnects can exhibit a typical line resistance of 0.45 mΩ/square (1 oz. Cu, for example). Force and sense connections, also referred to as Kelvin connections, offer a convenient method of eliminating the effects of voltage drops in circuit wires. Load currents flowing through wiring resistance produce an error ($V_{ERROR} = R \times I_L$) at the load. However, the Kelvin connection of Figure 7 overcomes the problem by including the wiring resistance within the forcing loop of the op amp. Since the op amp senses the load voltage, op amp loop control forces the output to compensate for the wiring error and to produce the correct voltage at the load.

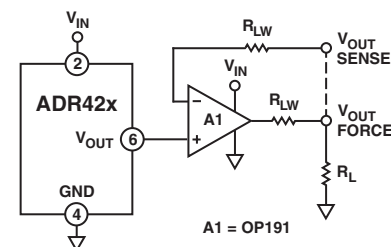


Figure 7. Advantage of Kelvin Connection

ADR420/ADR421/ADR423/ADR425

Dual Polarity References

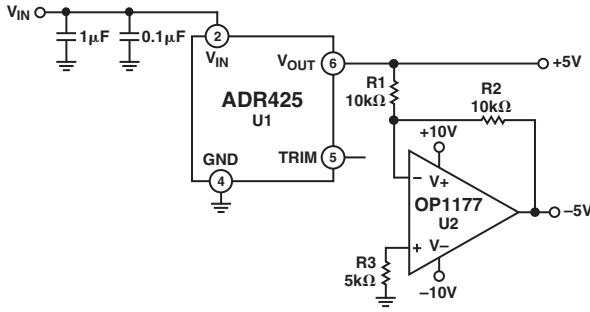


Figure 8. +5 V and -5 V Reference Using ADR425

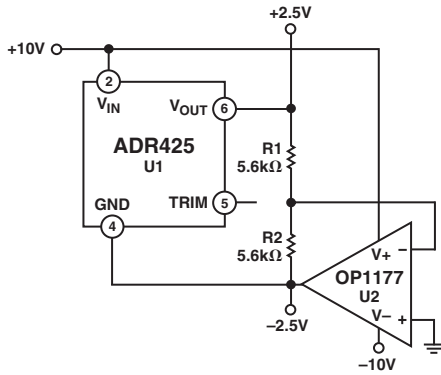


Figure 9. +2.5 V and -2.5 V Reference Using ADR425

Dual polarity references can easily be made with an op amp and a pair of resistors. In order not to defeat the accuracy obtained by ADR42x, it is imperative to match the resistance tolerance as well as the temperature coefficient of all the components.

Programmable Current Source

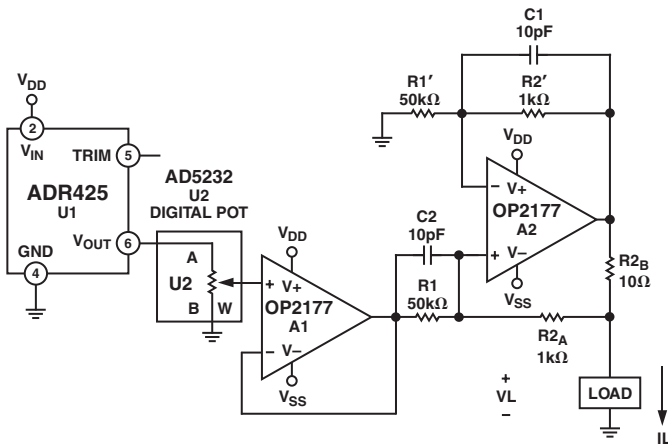


Figure 10. Programmable Current Source

Together with a digital potentiometer and a Howland current pump, ADR425 forms the reference source for a programmable current as

$$I_L = \frac{R2_A + R2_B}{R2_B} \times V_W \quad (3)$$

and

$$V_W = \frac{D}{2^N} \times V_{REF} \quad (4)$$

where

D = Decimal Equivalent of the Input Code

N = Number of Bits

In addition, $R1'$ and $R2'$ must be equal to $R1$ and $R2_A + R2_B$, respectively. $R2_B$ in theory can be made as small as needed to achieve the current needed within A_2 output current driving capability. In this example, OP2177 is able to deliver a maximum of 10 mA. Since the current pump employs both positive and negative feedback, capacitors $C1$ and $C2$ are needed to ensure the negative feedback prevails and, therefore, avoids oscillation. This circuit also allows bidirectional current flow if the inputs V_A and V_B of the digital potentiometer are supplied with the dual polarity references as shown previously.

Programmable DAC Reference Voltage

With a multichannel DAC such as a Quad 12-bit voltage output DAC AD7398, one of its internal DACs and an ADR42x voltage reference can be served as a common programmable V_{REFX} for the rest of the DACs. The circuit configuration is shown in Figure 11. The relationship of V_{REFX} to V_{REF} depends upon the digital code and the ratio of $R1$ and $R2$ and is given by:

$$V_{REFX} = \frac{V_{REF} \times \left(1 + \frac{R2}{R1}\right)}{\left(1 + \frac{D}{2^N} \times \frac{R2}{R1}\right)} \quad (5)$$

where

D = Decimal Equivalent of Input Code and

N = Number of Bits

V_{REF} = Applied External Reference

V_{REFX} = Reference Voltage for DAC A to D

Table III. V_{REFX} vs. R1 and R2

R1, R2	Digital Code	V_{REF}
R1 = R2	0000 0000 0000	$2 V_{REF}$
R1 = R2	1000 0000 0000	$1.3 V_{REF}$
R1 = R2	1111 1111 1111	V_{REF}
R1 = 3R2	0000 0000 0000	$4 V_{REF}$
R1 = 3R2	1000 0000 0000	$1.6 V_{REF}$
R1 = 3R2	1111 1111 1111	V_{REF}

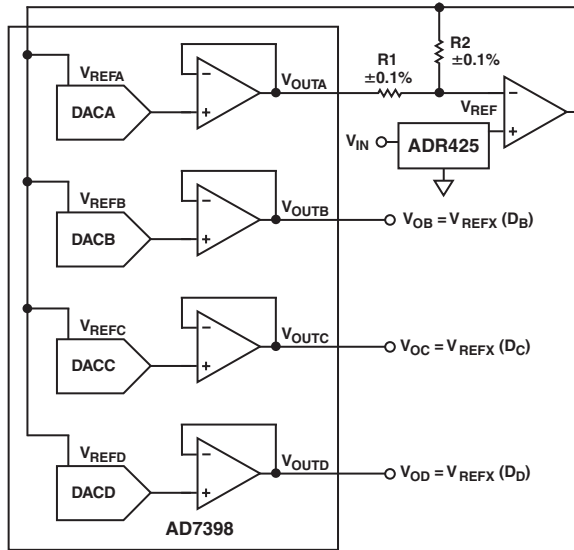


Figure 11. Programmable DAC Reference

Precision Voltage Reference for Data Converters

The ADR42x family has a number of features that make it ideal for use with A/D and D/A converters. The exceptional low noise, tight temperature coefficient, and high accuracy characteristics make the ADR42x ideal for low noise applications such as cellular base station applications.

Another example of ADC for which the ADR421 is also well-suited is the AD7701. Figure 12 shows the ADR421 used as the precision reference for this converter. The AD7701 is a 16-bit A/D converter with on-chip digital filtering intended for the measurement of wide dynamic range and low frequency signals such as those representing chemical, physical, or biological processes. It contains a charge-balancing (sigma-delta) ADC, calibration microcontroller with on-chip static RAM, a clock oscillator, and a serial communications port.

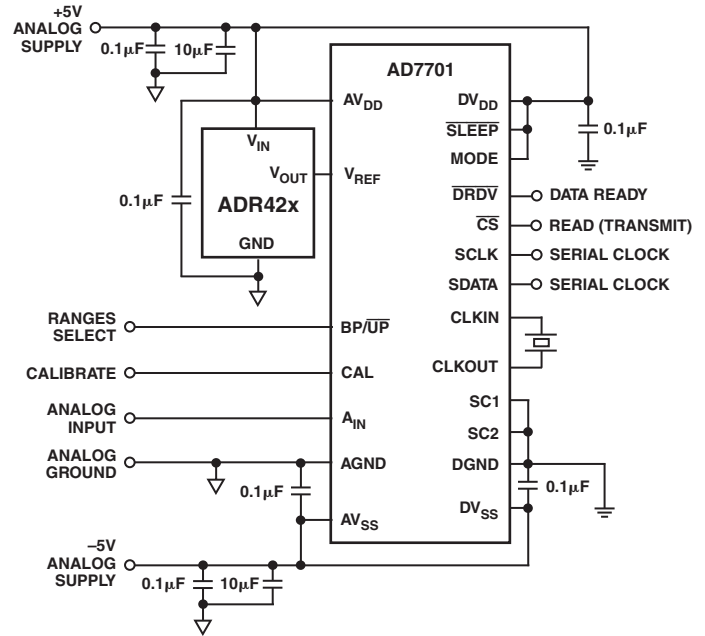


Figure 12. Voltage Reference for 16-Bit A/D Converter AD7701

Precision Boosted Output Regulator

A precision voltage output with boosted current capability can be realized with the circuit shown in Figure 13. In this circuit, U_2 forces V_O to be equal to V_{REF} by regulating the turn on of N_1 , therefore, the load current will be furnished by V_{IN} . In this configuration, a 50 mA load is achievable at V_{IN} of 5 V. Moderate heat will be generated on the MOSFET and higher current can be achieved with a replacement of the larger device. In addition, for heavy capacitive load with step input, a buffer may be added at the output to enhance the transient response.

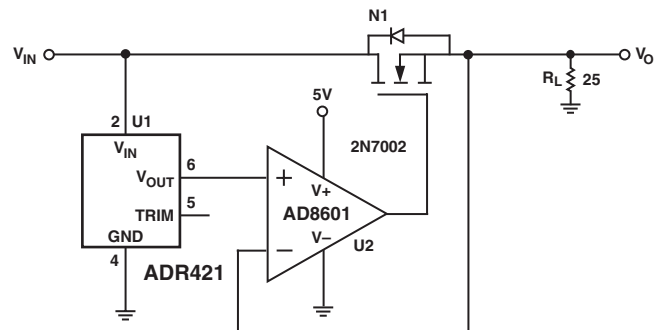
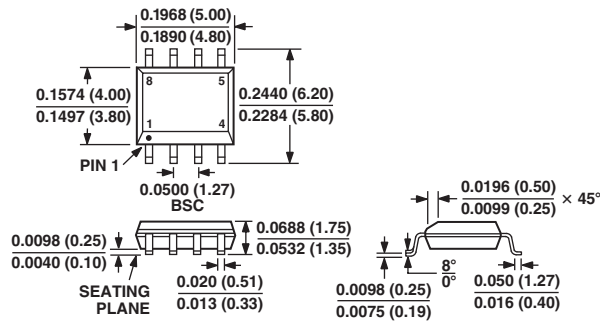


Figure 13. Precision Boosted Output Regulator

ADR420/ADR421/ADR423/ADR425

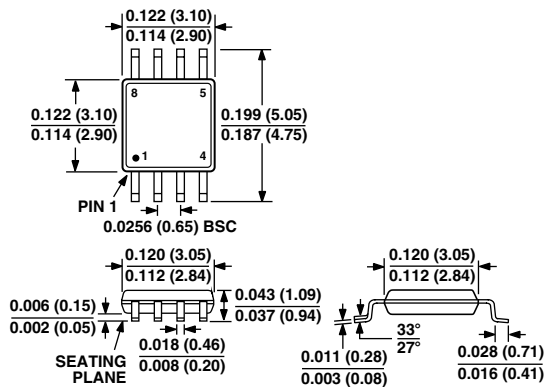
OUTLINE DIMENSIONS
Dimensions shown in inches and (mm).

8-Lead Narrow Body SOIC
(R-8)



- NOTES
1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS
2. ALL DIMENSIONS PER JEDEC STANDARDS MS-012 AA

8-Lead Mini_SOIC
(RM-8)



Revision History

Location	Page
03/02—Data Sheet changed from REV. A to REV. B.	
Edits to ORDERING GUIDE	4
Deletion of Precision Voltage Regulator section	15
Addition of Precision Boosted Output Regulator section	15
Addition of Figure 13	15
Data Sheet changed from REV. 0 to REV. A.	
Addition of ADR423 and ADR425 to ADR420/ADR421	Universal